

# Device Modeling Report

COMPONENTS:  
DIODE/ GENERAL PURPOSE RECTIFIER / STANDARD  
PART NUMBER: RHRP30120  
MANUFACTURER: INTERSIL  
REMARK: TC=150C

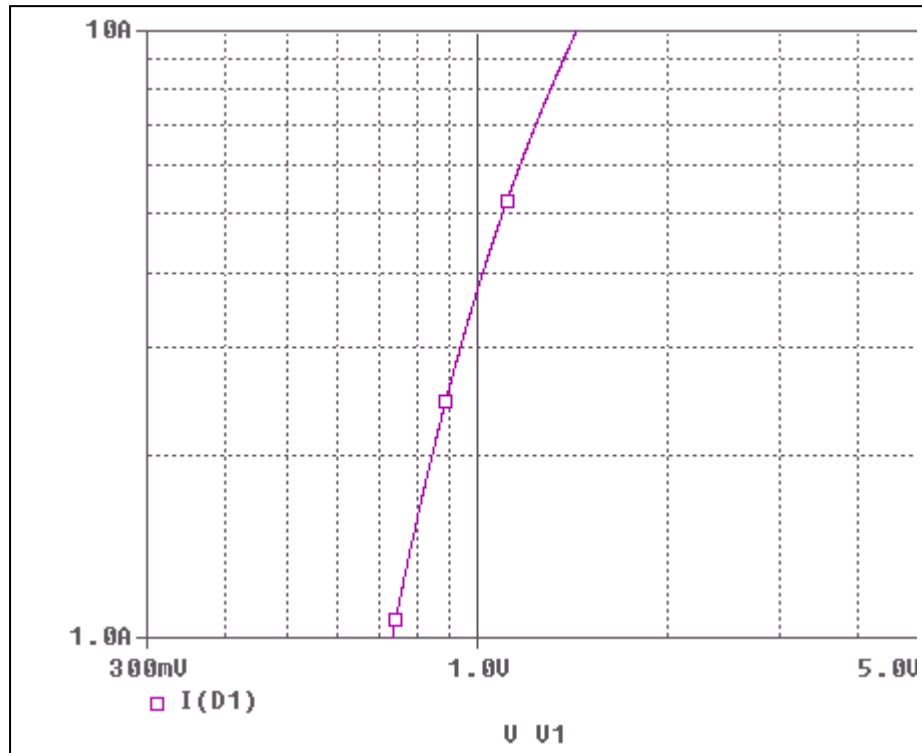


**Bee Technologies Inc.**

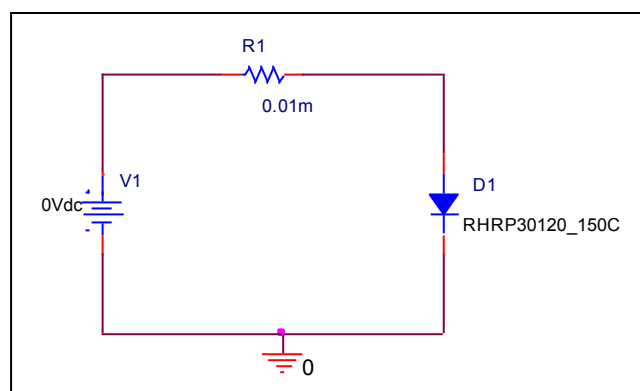
| PSpice model parameter | Model description                           |
|------------------------|---------------------------------------------|
| IS                     | Saturation Current                          |
| N                      | Emission Coefficient                        |
| RS                     | Series Resistance                           |
| IKF                    | High-injection Knee Current                 |
| CJO                    | Zero-bias Junction Capacitance              |
| M                      | Junction Grading Coefficient                |
| VJ                     | Junction Potential                          |
| ISR                    | Recombination Current Saturation Value      |
| BV                     | Reverse Breakdown Voltage(a positive value) |
| IBV                    | Reverse Breakdown Current(a positive value) |
| TT                     | Transit Time                                |
| EG                     | Energy-band Gap                             |

## Forward Current Characteristic

### Circuit Simulation Result

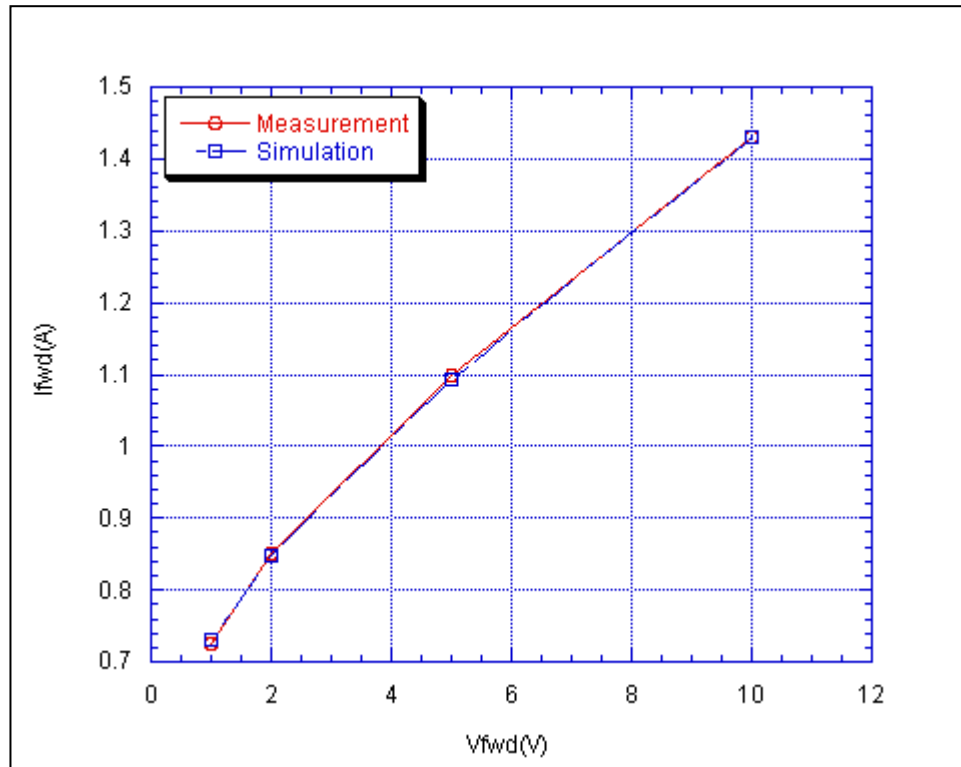


### Evaluation Circuit



## Comparison Graph

### Circuit Simulation Result

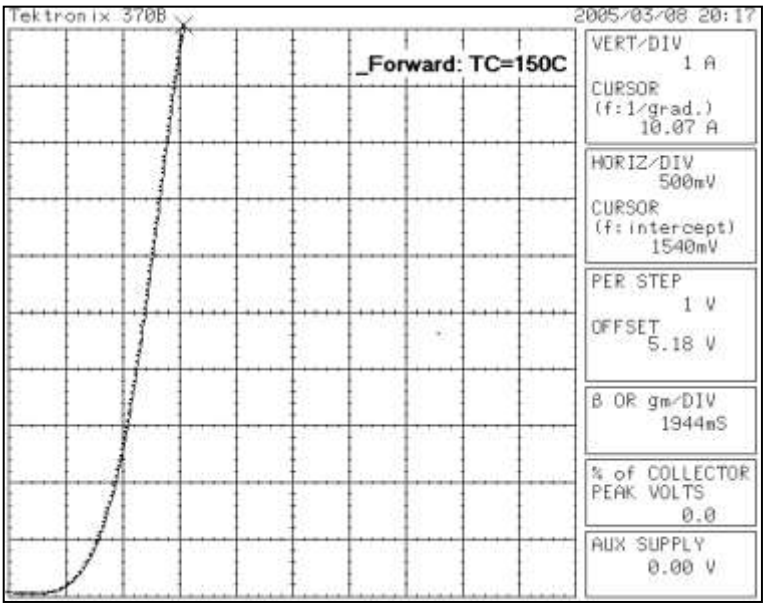


### Simulation Result

| $I_{fwd}$ (A) | $V_{fwd}$ (V)<br>Measurement | $V_{fwd}$ (V)<br>Simulation | %Error |
|---------------|------------------------------|-----------------------------|--------|
| 1             | 0.725                        | 0.732                       | -0.97  |
| 2             | 0.850                        | 0.847                       | 0.35   |
| 5             | 1.100                        | 1.093                       | 0.64   |
| 10            | 1.430                        | 1.430                       | 0.00   |

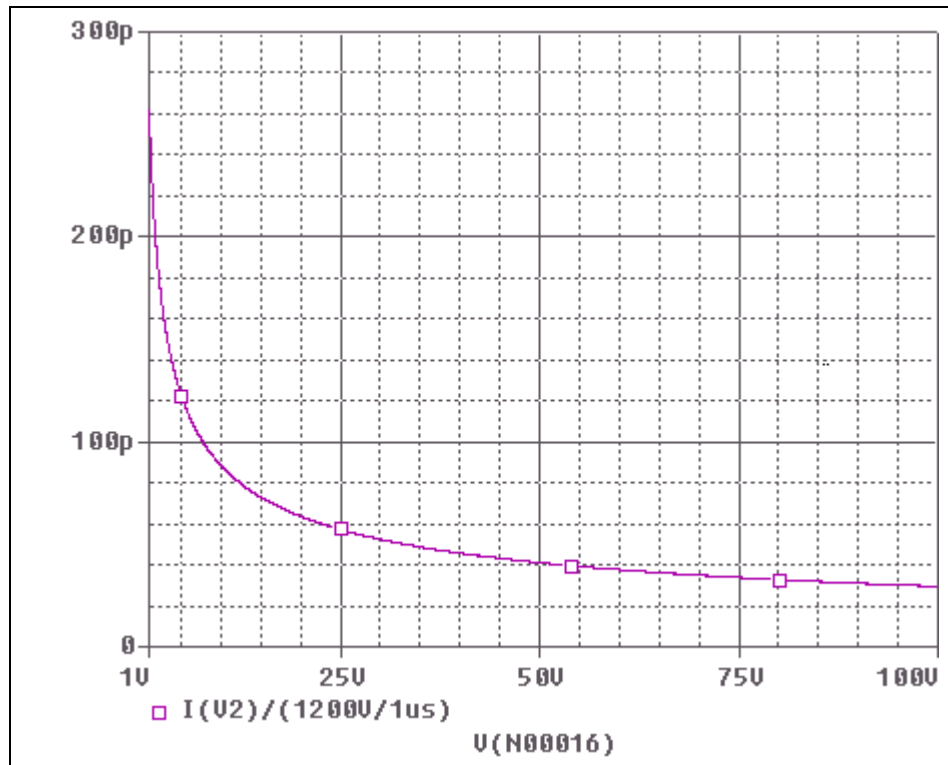
Forward Current Characteristic

Reference

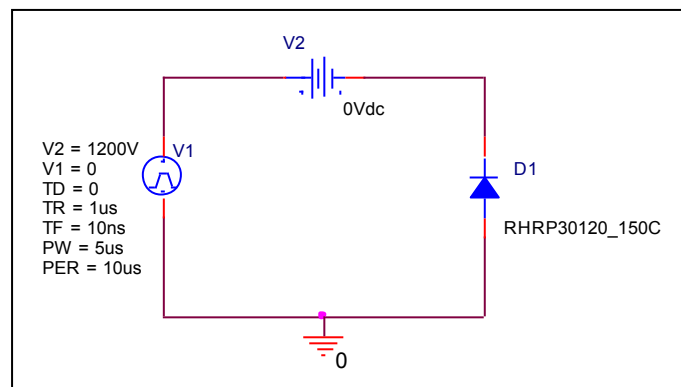


# Capacitance Characteristic

## Circuit Simulation Result

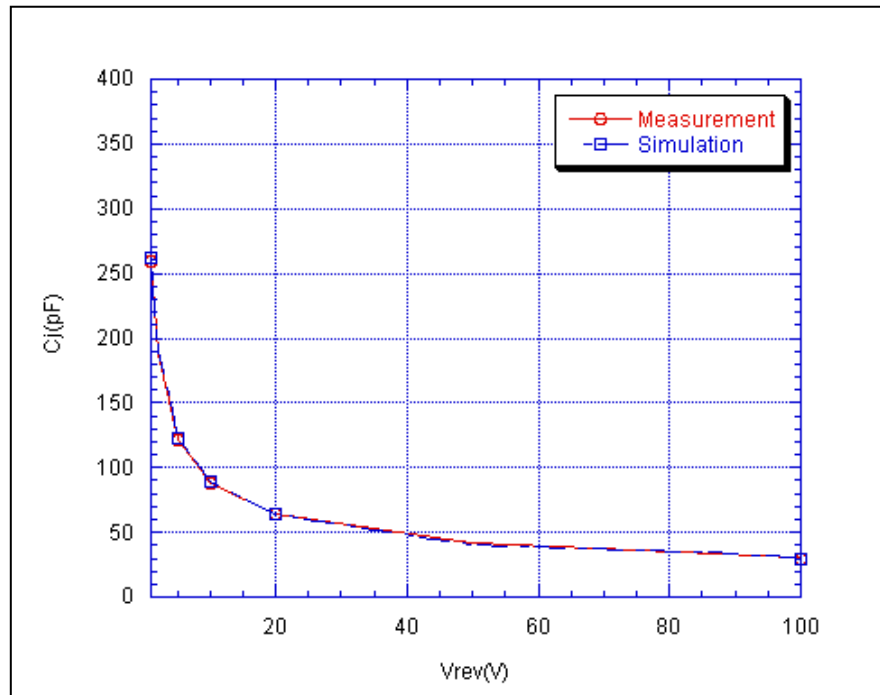


## Evaluation Circuit



## Comparison Graph

### Circuit Simulation Result

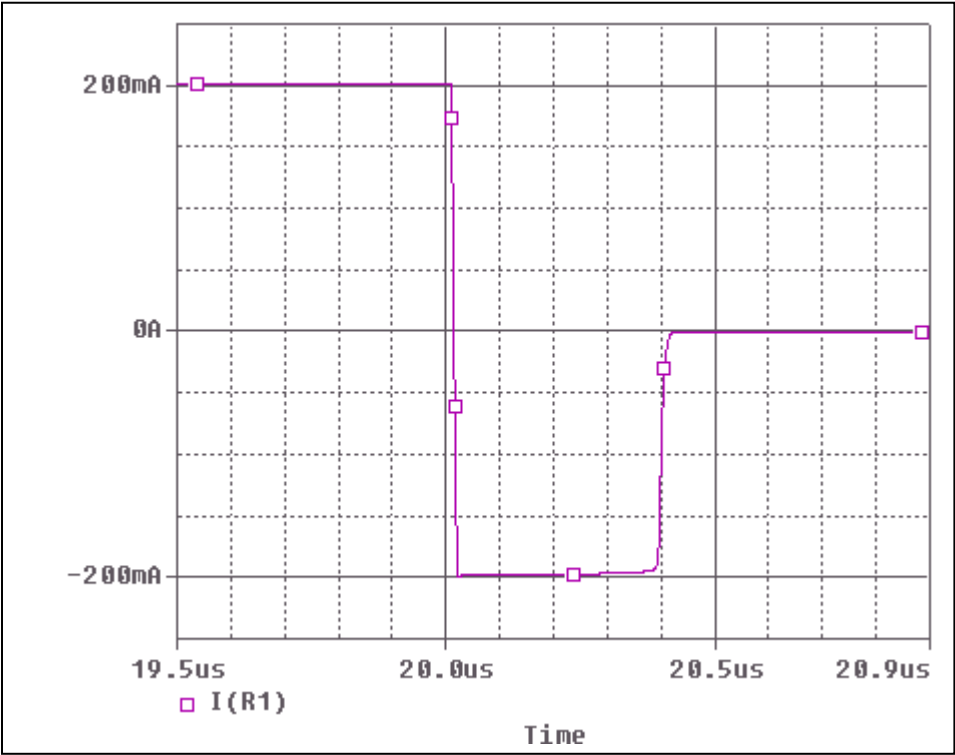


### Simulation Result

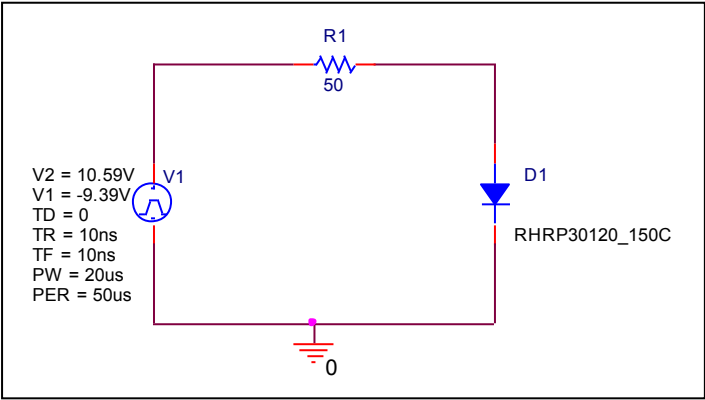
| Vrev(V) | Cj(pF)<br>Measurement | Cj(pF)<br>Simulation | %Error |
|---------|-----------------------|----------------------|--------|
| 0       | 571.000               | 571.000              | 0.00   |
| 1       | 259.000               | 262.245              | -1.25  |
| 2       | 188.000               | 189.633              | -0.87  |
| 5       | 122.000               | 123.176              | -0.96  |
| 10      | 88.000                | 88.609               | -0.69  |
| 20      | 64.000                | 63.585               | 0.65   |
| 50      | 42.000                | 41.011               | 2.35   |
| 100     | 30.000                | 29.409               | 1.97   |

# Reverse Recovery Characteristic

## Circuit Simulation Result



## Evaluation Circuit



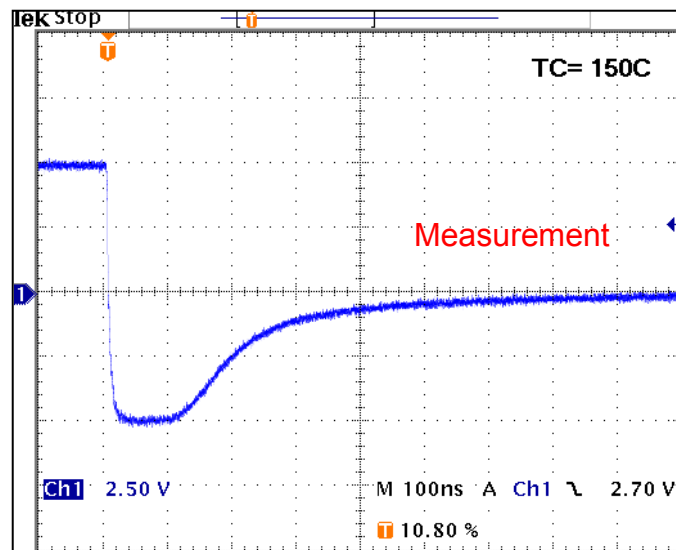
## Compare Measurement vs. Simulation

|     | Measurement |    | Simulation |    | %Error |
|-----|-------------|----|------------|----|--------|
| trr | 392.00      | ns | 393.29     | ns | 0.073  |



## Reverse Recovery Characteristic

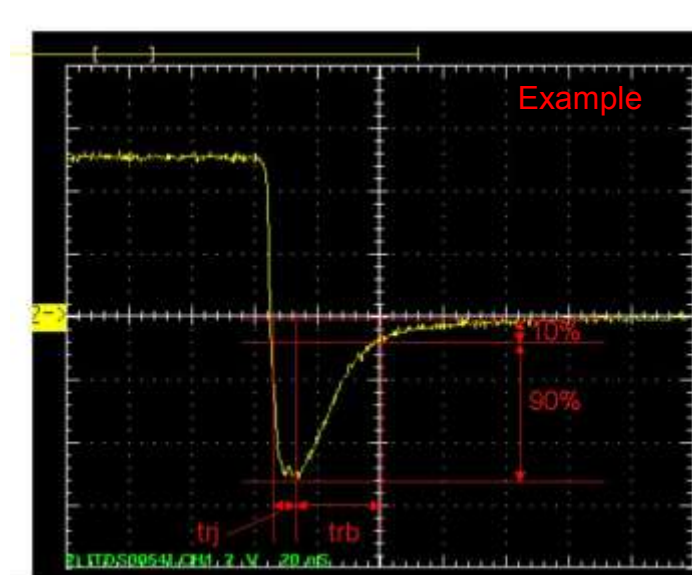
## Reference



$T_{rj} = 96 \text{ (ns)}$

$T_{rb} = 296 \text{ (ns)}$

Conditions:  $I_{fwd} = I_{rev} = 0.2 \text{ (A)}$ ,  $R_I = 50$



Relation between  $t_{rj}$  and  $t_{rb}$